

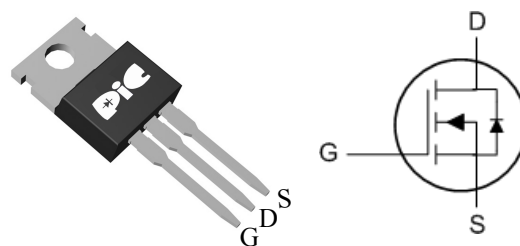
➤ General Description

This PAN00SG76AG N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology
- TO-220 package design

➤ TO-220



➤ Application

- High Frequency Switching and Synchronous Rectification
- DC/DC Converter

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{1,6}	$I_D@T_C=25^\circ C$	308	A
Continuous Drain Current ^{1,6}	$I_D@T_C=100^\circ C$	218	A
Pulsed Drain Current ²	I_{DM}	550	A
Single Pulse Avalanche Energy ³	EAS	1012.5	mJ
Avalanche Current	I_{AS}	45	A
Total Power Dissipation ⁴	$P_D@T_C=25^\circ C$	429	W
Storage Temperature Range	T_{STG}	-55 to 175	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 175	$^\circ C$
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	60	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	0.35	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	BV_{DSS}	100	---	---	V
Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=30A$	$R_{DS(ON)}$	---	1.8	2.2	$m\Omega$
Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	$V_{GS(th)}$	2	---	4	V
Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=25^\circ C$	I_{DSS}	---	---	1	μA
	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=100^\circ C$		---	---	100	
Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	I_{GSS}	---	---	± 100	nA
Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	g_{fs}	---	75	---	S
Total Gate Charge	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=20A$	Q_g	---	200	---	nC
Gate-Source Charge		Q_{gs}	---	53.3	---	
Gate-Drain Charge		Q_{gd}	---	49	---	
Turn-On Delay Time	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3\Omega$, $I_D=20A$	$T_{d(on)}$	---	47	---	ns
Rise Time		T_r	---	28	---	
Turn-Off Delay Time		$T_{d(off)}$	---	79	---	
Fall Time		T_f	---	18	---	
Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $f=1MHz$	C_{iss}	---	13362	---	pF
Output Capacitance		C_{oss}	---	1917	---	
Reverse Transfer Capacitance		C_{rss}	---	387	---	

➤ Diode Characteristics

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5,6}	$V_G=V_D=0V$, Force Current	I_S	---	---	80	A
Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ C$	V_{SD}	---	---	1.1	V
Reverse Recovery Time	$I_F=20A$, $di/dt=100A/\mu s$, $T_J=25^\circ C$	t_{rr}	---	70	---	nS
Reverse Recovery Charge		Q_{rr}	---	580	---	nC

Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=1.0mH$, $I_{AS}=45A$
4. Ensure that the channel temperature does not exceed $150^\circ C$.
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
6. Bonding wire limitation current is 120A.

➤ Typical Characteristics

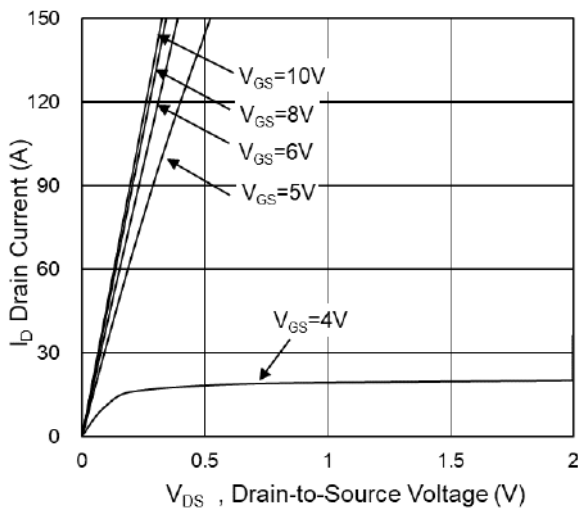


Fig.1 Typical Output Characteristics

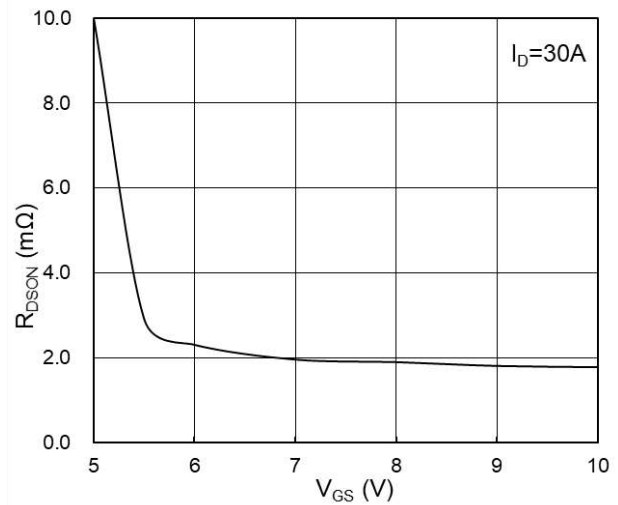


Fig.2 On-Resistance vs G-S Voltage

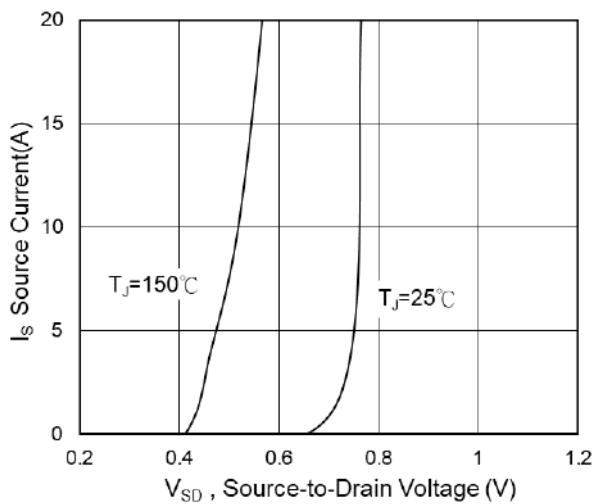


Fig.3 Source-Drain Forward Characteristics

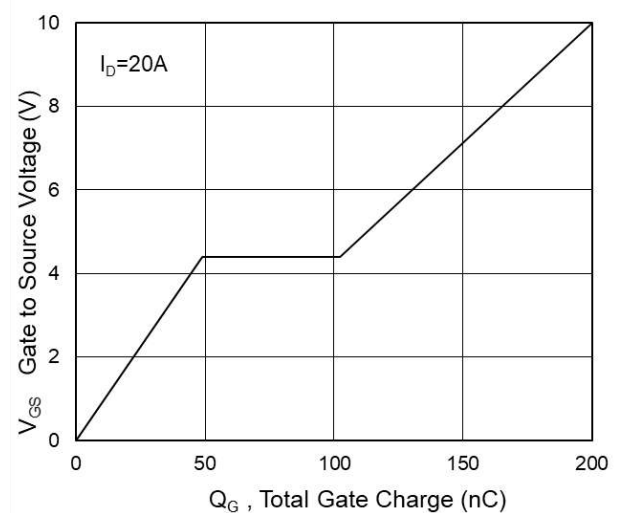


Fig.4 Gate-Charge Characteristics

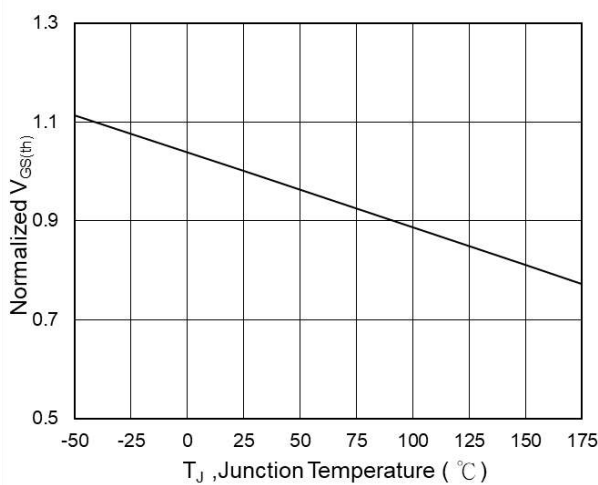


Fig.5 Normalized $V_{GS(th)}$ vs T_J

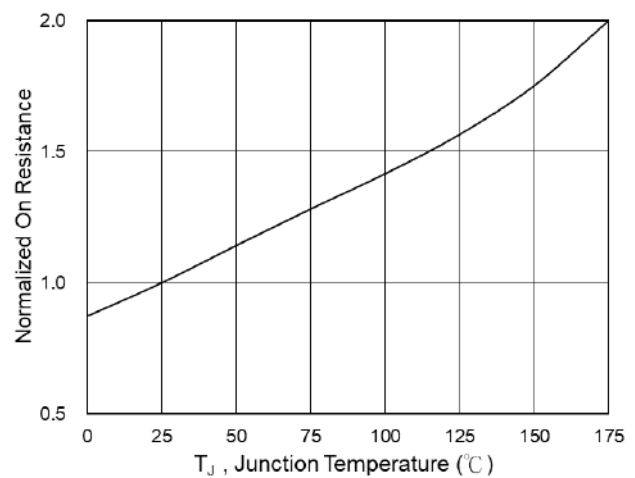


Fig.6 Normalized $R_{DS(ON)}$ vs T_J

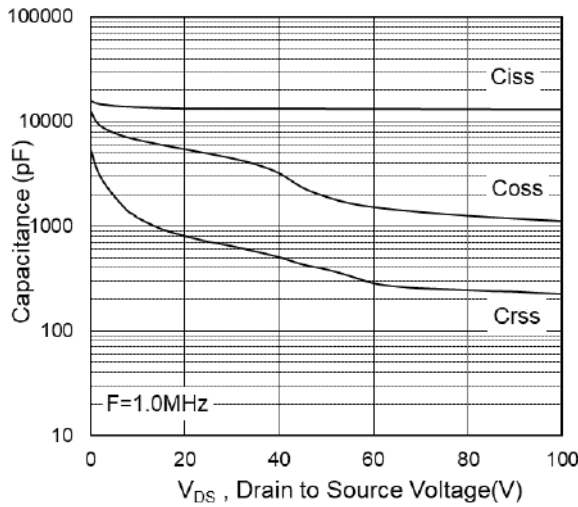


Fig.7 Capacitance

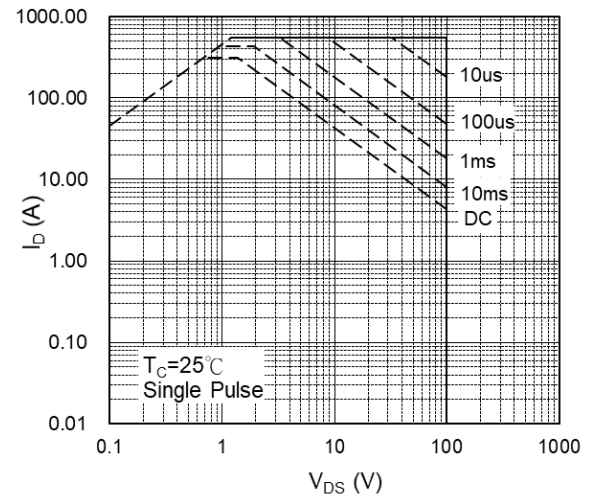


Fig.8 Safe Operating Area

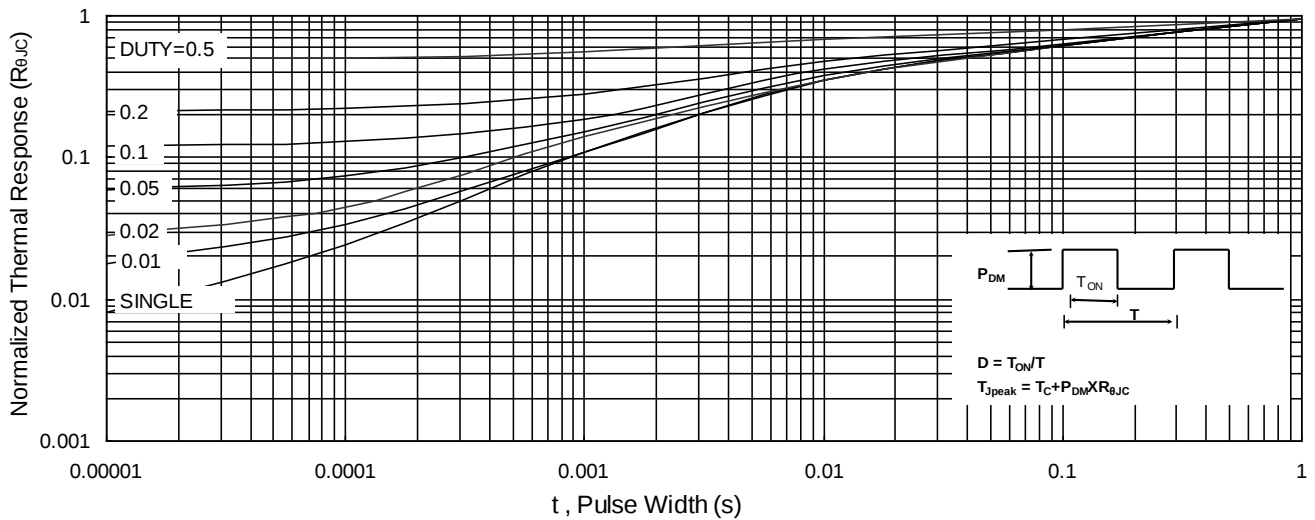


Fig.9 Normalized Maximum Transient Thermal Impedance

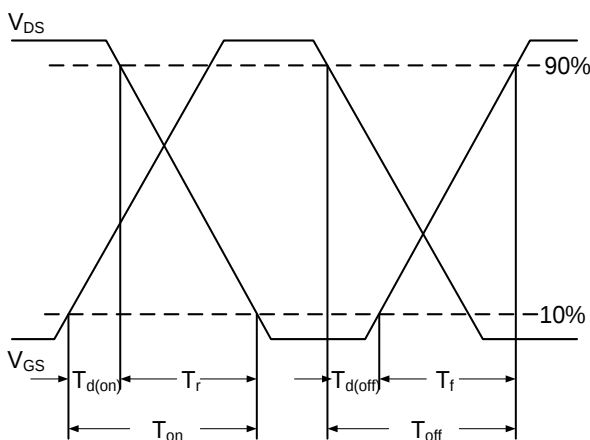


Fig.10 Switching Time Waveform

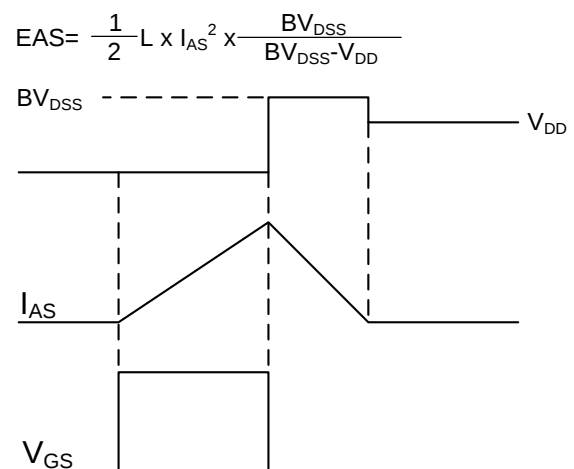
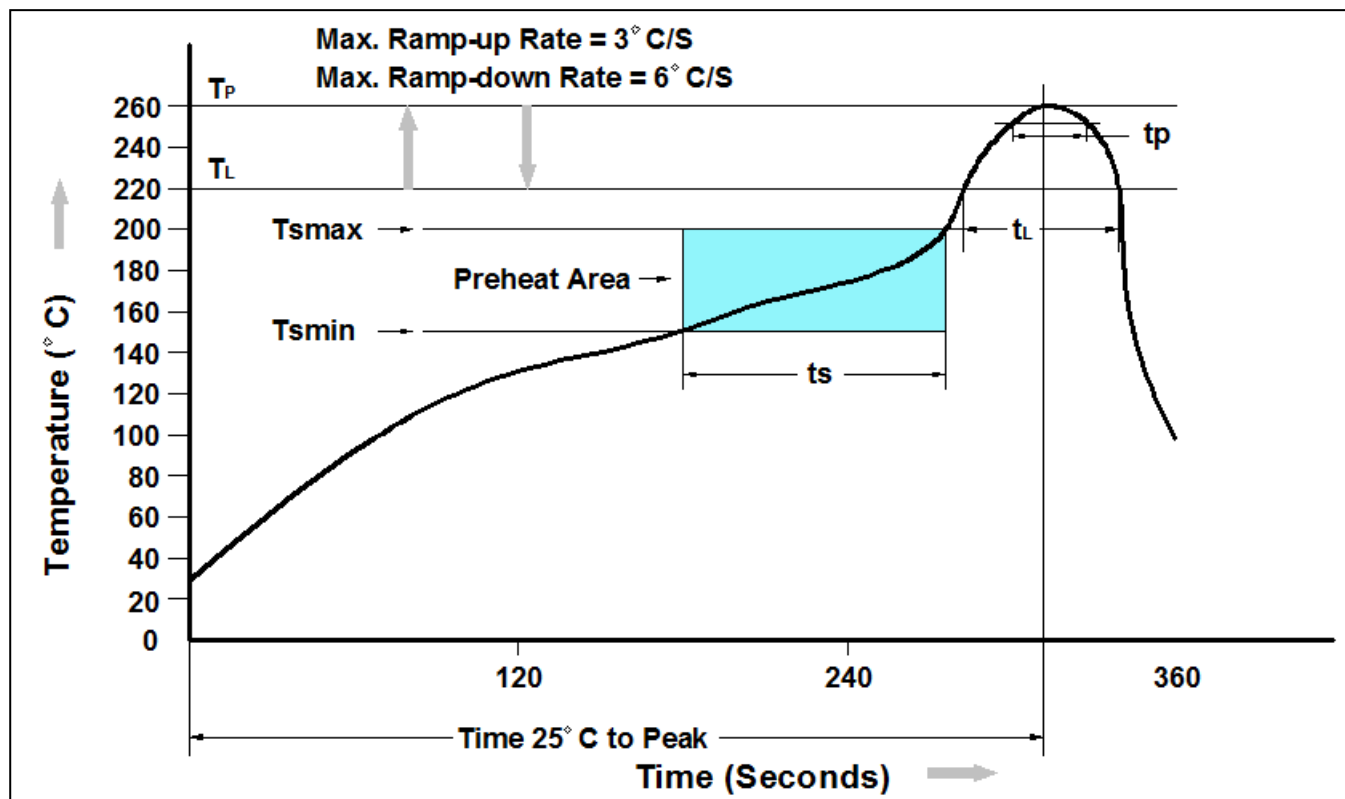


Fig.11 Unclamped Inductive Switching Waveform

➤ Recommend IR Reflow Soldering Thermal Profile

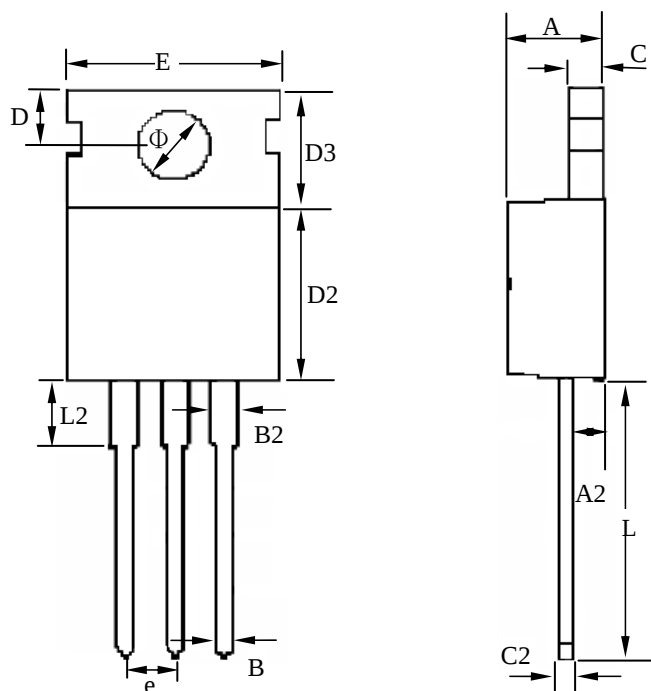


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (ts) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN00SG76AG	TO-220	50 pcs/tube

➤ Package Information (TO-220)



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.25	--	4.80	0.167	--	0.189
A2	2.20	--	2.92	0.087	--	0.115
B	0.70	--	0.91	0.028	--	0.036
B2	1.15	--	1.77	0.045	--	0.070
C	1.20	--	1.40	0.047	--	0.055
C2	0.45	--	0.61	0.018	--	0.024
D	2.54	--	3.00	0.100	--	0.118
D2	8.39	--	9.47	0.330	--	0.373
D3	6.30	--	6.70	0.248	--	0.264
E	9.70	--	10.36	0.382	--	0.408
L	12.75	--	14.40	0.502	--	0.567
L2	2.45	--	4.05	0.096	--	0.159
Φ	3.50	--	3.80	0.138	--	0.150
e	--	2.54	--	--	0.100	--

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